BROADBAND POWER AMPLIFIER
ABP0300-02-3325

Features:

- Broad band, medium power, and high gain
- Low VSWR, unconditional stable
- Small size, low cost
- SMA female connector I/O
- Operating temperature -40~+75°C, storage temperature -55~+85°C

General Description

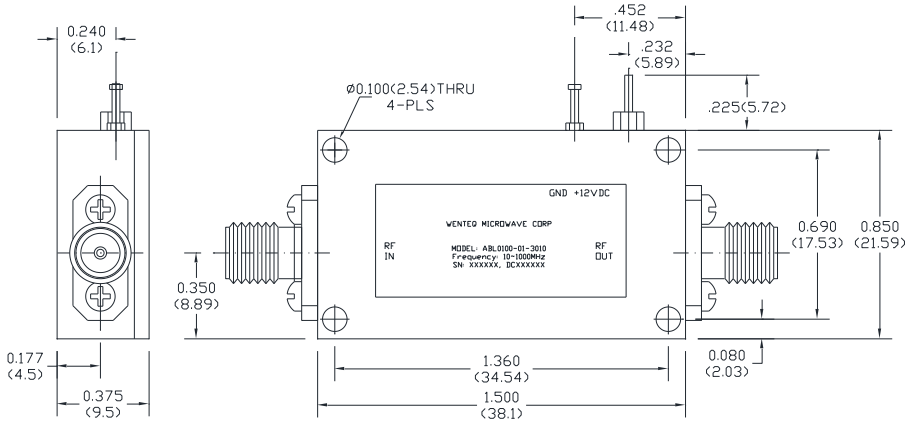
ABP0300-02-3325 is a two-stage enhancement pHEMT technology based broadband power amplifier module operating in the frequency from 50MHz to 3.0GHz. The amplifier provides 33dB of small signal gain, and +25dBm output P-1dB power, as well as good VSWR at both input and output. The amplifier requires only a single positive DC power supply. Its built-in DC voltage regulator allows the amplifier to functional at different DC supply voltages without affecting the RF performances.

Electrical Specifications

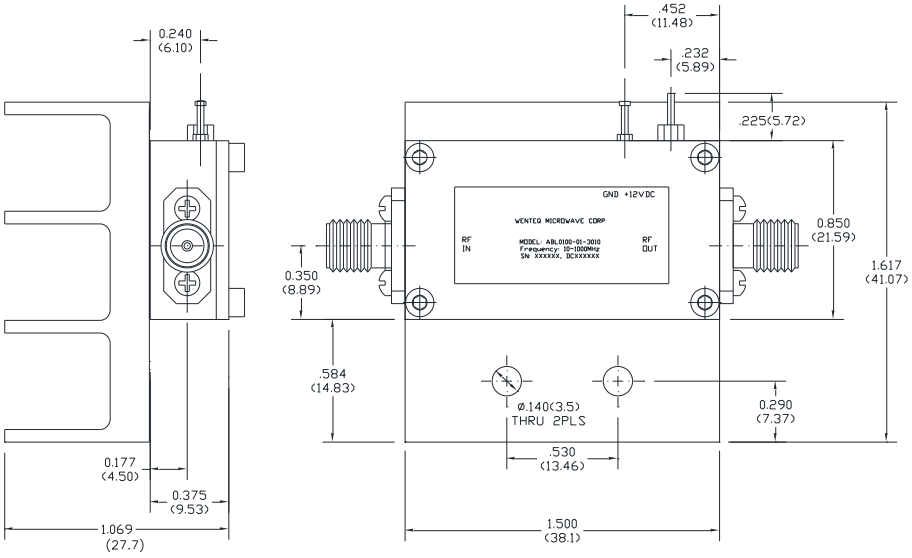
Parameters	Units	Specifications		
		Minimum	Typical	Maximum
Frequency Range	GHz	0.05		3.0
Small Signal Gain @25°C	dB	30.0	33.0	36.0
Noise Figure	dB		4.5	5.5
P-1dB Compression Point	dBm	+23.0	+25.0	
Output IP3	dBm	+37.0	+42.0	
Gain flatness	dB		+/-1.0	+/-1.5
Gain Variation	dB		+/-1.0	
Input VSWR	-		1.5:1	2.2:1
Output VSWR	-		1.5:1	2.2:1
Reverse Isolation	dB	45.0		
Non-Harmonic Spurious	dBc			-70.0
Operating Temperature	°C	-40		+85
Survival Temperature	°C	-55		+125
DC Voltage	V		+12	
DC Supply Current	mA	200	240	280
RF In/Out connectors		50 ohm SMA Female Connectors		
Outline dimension for ABP0300-03-3325 without heatsink	inches	1.5x0.85x0.375		
Outline dimension for ABP0300-02-3325-X with heatsink	inches	1.50×1.617×1.069		

138 W Pomona Ave, Monrovia, CA 91016
Phone: (626) 305-6666, Fax: (626) 602-3101, sales@wenteq.com, www.wenteq.com

Mechanical Structure:



(a) ABP0300-02-3325 Amplifier without heatsink



(b) ABP0300-02-3325-X amplifier with heatsink

Note: All units are in inches(mm), and all tolerances are +/-0.005 inch unless otherwise specified